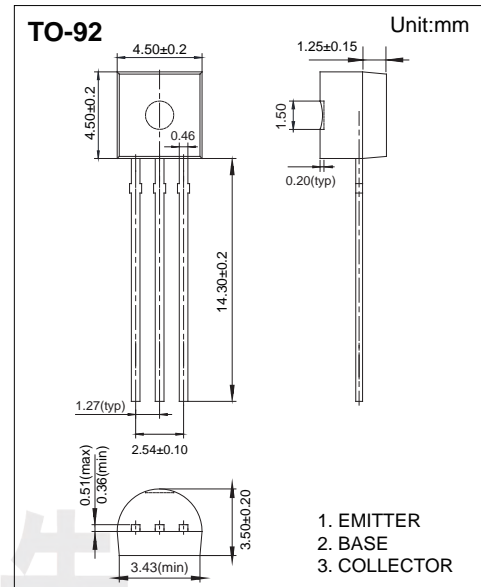


Transistor

PNP Transistors S8550

■ Features

- High Total Power Dissipation. ($P_C=625mW$)
- Collector current: $I_C=-0.5A$
- Excellent hFE Linearity



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-40	V
Collector - Emitter Voltage	V_{CEO}	-25	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-0.5	A
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collecto- base breakdown voltage	V_{CBO}	$I_C = -100 \mu A, I_E = 0$	-40			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = -1 mA, I_B = 0$	-25			
Emitter - base breakdown voltage	V_{EBO}	$I_E = -100 \mu A, I_C = 0$	-5			
Collector cut-off current	I_{CBO}	$V_{CB} = -40V, I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -20V, I_E = 0$			-0.1	
Emitter cut-off current	I_{EBO}	$V_{EB} = -3V, I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500 mA, I_B = -50mA$			-0.6	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500 mA, I_B = -50mA$			-1.2	
DC current gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -50mA$	85		400	
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -500mA$	50			
Transition frequency	f_T	$V_{CE} = -6V, I_C = -20mA, f = 30MHz$	150			MHz

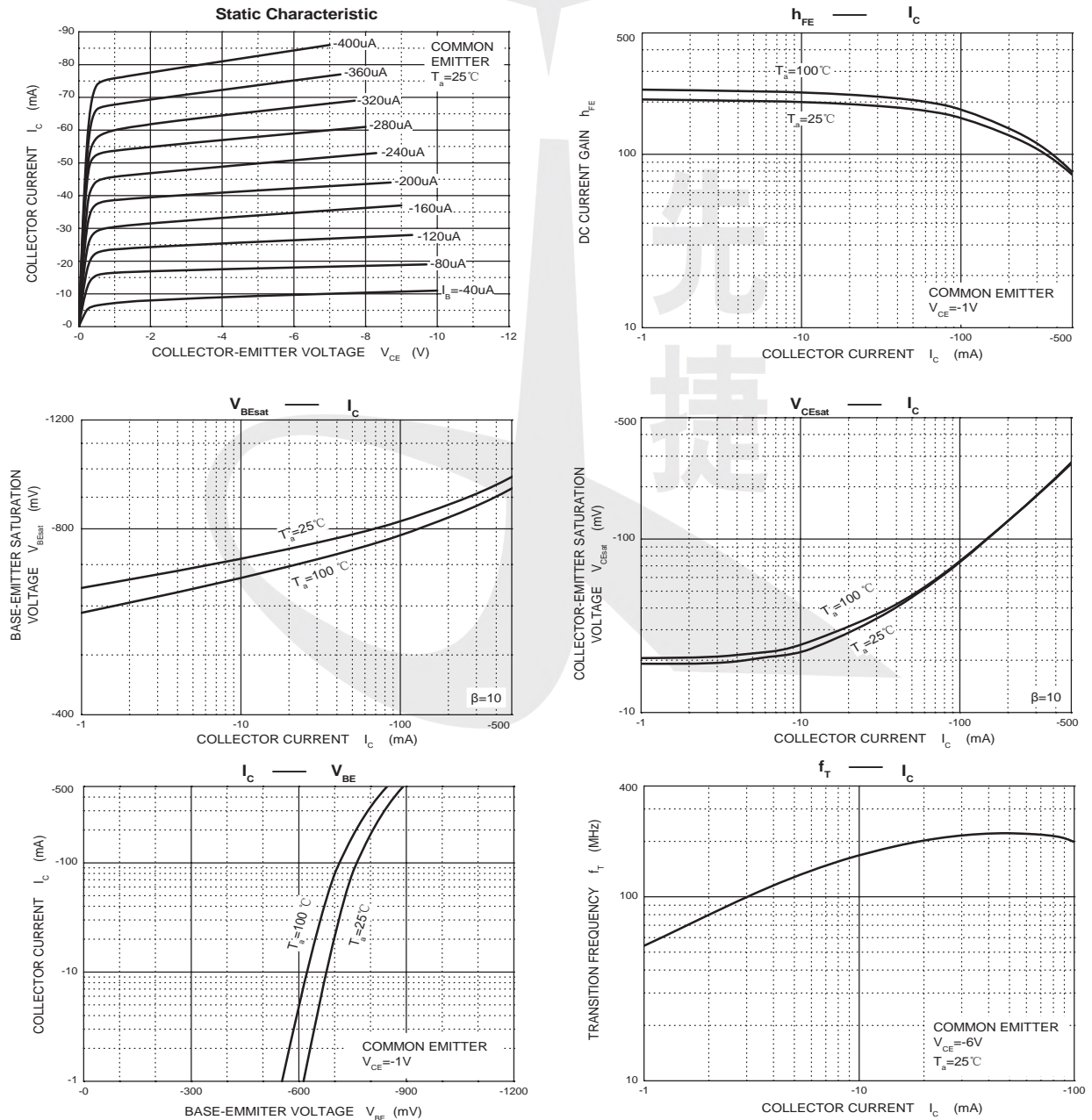
Transistor

PNP Transistors S8550

Classification of hFE(1)

Rank	B	C	D	D3
Range	85-160	120-200	160-300	300-400

Typical Characteristics

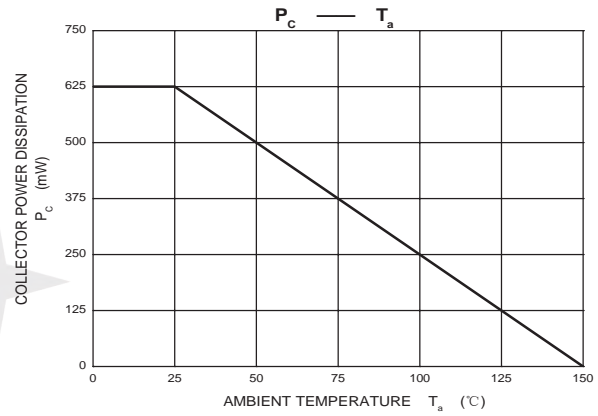
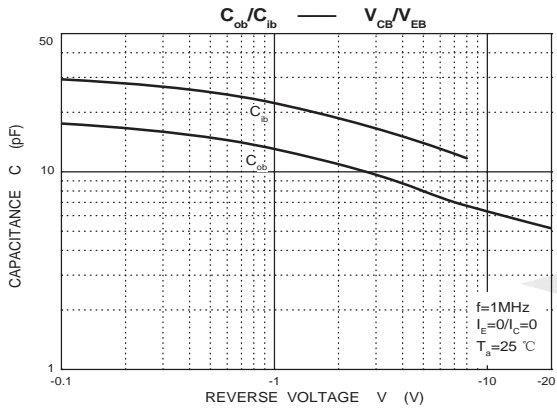


Transistor

PNP Transistors

S8550

■ Typical Characteristics



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